

2SB860

Silicon PNP Triple Diffused

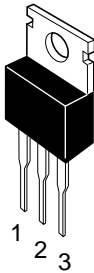
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Application

Low frequency power amplifier TV vertical deflection output complementary pair with 2SD1137

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

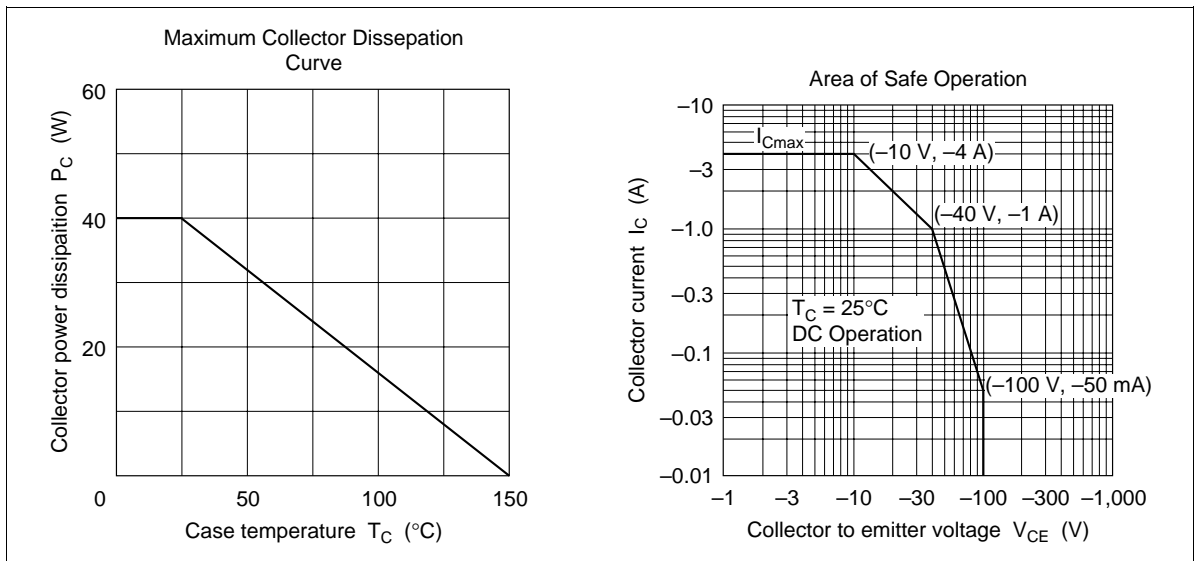
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-100	V
Collector to emitter voltage	V_{CEO}	-100	V
Emitter to base voltage	V_{EBO}	-4	V
Collector current	I_C	-4	A
Collector peak current	$I_{C(peak)}$	-5	A
Collector power dissipation	P_C	1.8	W
	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-45 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

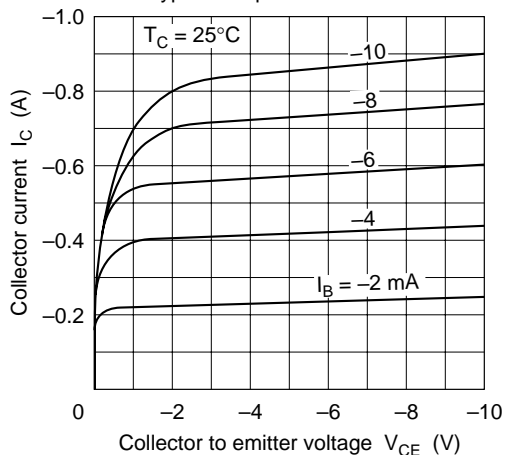
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	V	$I_C = -10 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	—	—	V	$I_E = -1 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CEO}	—	—	-100	μA	$V_{CE} = -80 \text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	-50	μA	$V_{EB} = -3.5 \text{ V}$, $I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1.0	V	$I_C = -1 \text{ A}$, $I_B = -0.1 \text{ A}^{*1}$
DC current transfer ratio	h_{FE}	50	—	250		$V_{CE} = -4 \text{ V}$ $I_C = -0.5 \text{ A}^{*1}$
		25	—	350		

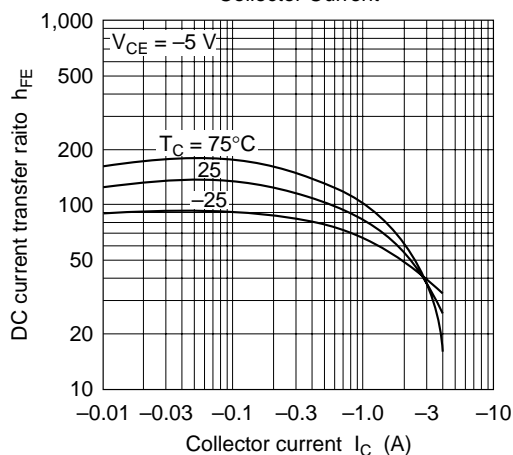
Note: 1. Pulse test



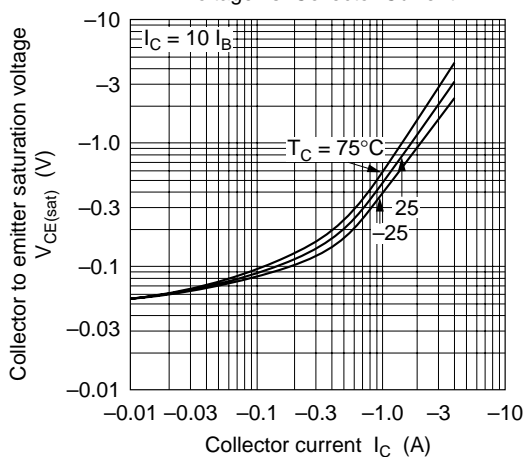
Typical Output Characteristics



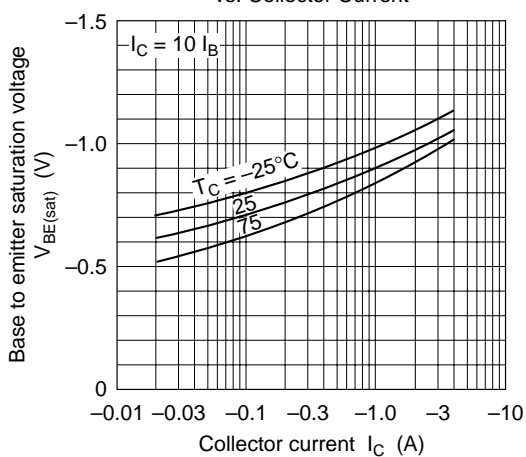
DC Current Transfer Ratio vs. Collector Current

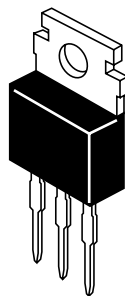
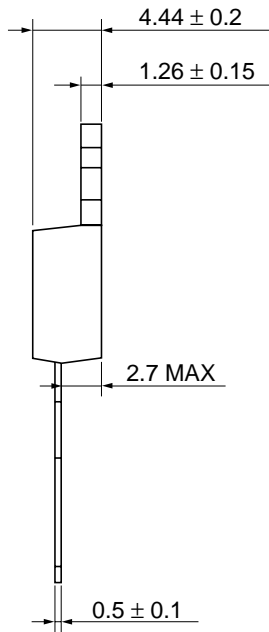
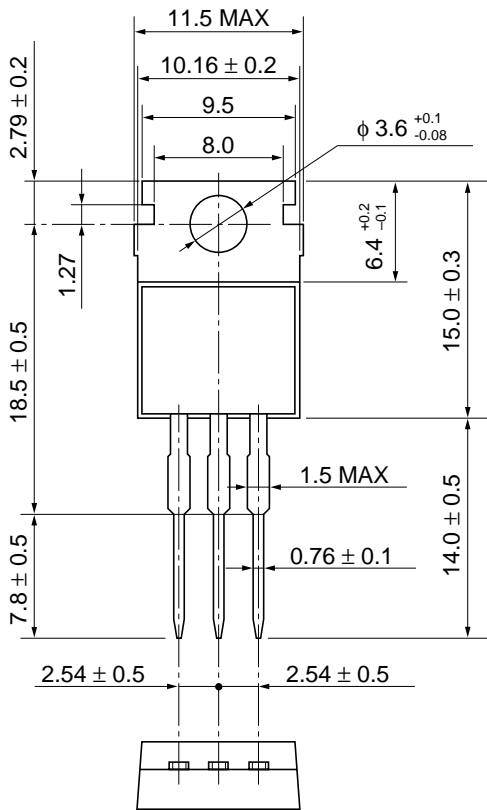


Collector to Emitter Saturation Voltage vs. Collector Current



Base to Emitter Saturation Voltage vs. Collector Current





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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